

KSA1010

High Speed High Voltage Switching

- Industrial Use
- Complement to KSC2334



1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	- 100	V
V _{CEO}	Collector-Emitter Voltage	- 100	V
V_{EBO}	Emitter-Base Voltage	- 7	V
I _C	Collector Current (DC)	- 7	Α
I _{CP}	*Collector Current (Pulse)	- 15	Α
I _B	Base Current	- 3.5	Α
P _C	Collector Dissipation (T _C =25°C)	40	W
P _C	Collector Dissipation (T _a =25°C)	1.5	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

^{*} PW≤300μs, Duty Cycle≤10%

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Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	$I_C = -5A$, $I_{B1} = -0.5A$, $L = 1mH$	- 100		V
V _{CEX} (sus)1	Collector-Emitter Sustaining Voltage	I_C = - 5A, I_{B1} = - I_{B2} = - 0.5A V_{BE} (off) = 5V, L = 180 μ H Clamped	- 100		V
V _{CEX} (sus)2	Collector-Emitter Sustaining Voltage	I_C = - 10A, I_{B1} = - 1A I_{B2} = 0.5A, V_{BE} (off) = 5V L = 180 μ H, Clamped	- 100		V
I _{CBO}	Collector Cut-off Current	V _{CB} = - 100V, I _E = 0		- 10	μΑ
I _{CER}	Collector Cut-off Current	$V_{CE} = -100V, R_{BE} = 51\Omega$ $T_{C} = 125^{\circ}C$		- 1	mA
I _{CEX1}	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$		- 10	μΑ
I _{CEX2}	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$ $T_{C} = 125^{\circ}C$		- 1	mA
I _{EBO}	Emitter Cut-off Current	V _{EB} = - 5V, I _C = 0		- 10	uA
h _{FE1} h _{FE2} h _{FE3}	* DC Current Gain	$V_{CE} = -5V, I_{C} = -0.5A$ $V_{CE} = -5V, I_{C} = -3A$ $V_{CE} = -5V, I_{C} = -5A$	40 40 20	200	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = - 5A, I _B = - 0.5A		- 0.6	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = - 5A, I _B = - 0.5A		- 1.5	V
t _{ON}	Turn On Time	V _{CC} = - 50V, I _C = - 5A,		0.5	μs
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = -0.5A$		1.5	μs
t _F	Fall Time	$R_L = 10\Omega$		0.5	μs

Pulse Test: PW≤350μs, Duty Cycle≤2%

\mathbf{h}_{FE} Classification

Classification	R	0	Y
h _{FE2}	40 ~ 80	60 ~ 120	100 ~ 200

Typical Characteristics

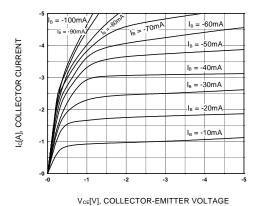


Figure 1. Static Characteristic

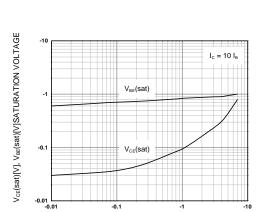


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

I_C[A], COLLECTOR CURRENT

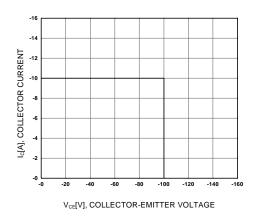


Figure 5. Reverse Bias Safe Operating Areas

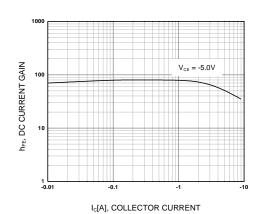


Figure 2. DC current Gain

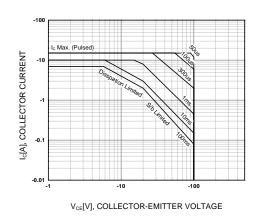


Figure 4. Safe Operating Area

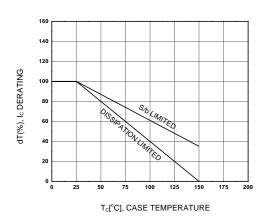


Figure 6. Derating Curve of Safe Operating Areas

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Typical Characteristics (continued)

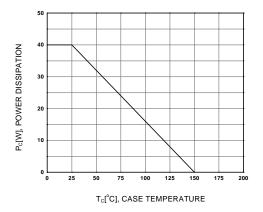
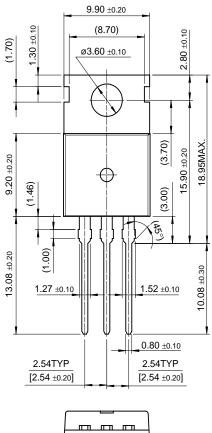


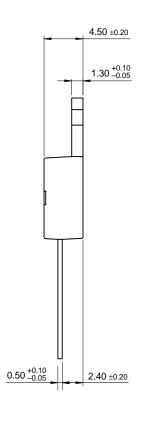
Figure 7. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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